

Rahim Faez

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

87

papers

591

citations

11

h-index

21

g-index

106

ext. papers

704

ext. citations

1.9

avg, IF

4.13

L-index

#	Paper	IF	Citations
87	Engineering enhanced thermoelectric properties in zigzag graphene nanoribbons. <i>Journal of Applied Physics</i> , 2012 , 111, 054501	2.5	71
86	Stability Analysis in Graphene Nanoribbon Interconnects. <i>IEEE Electron Device Letters</i> , 2010 , 31, 1458-1460	4.0	65
85	Geometrical effects on the thermoelectric properties of ballistic graphene antidot lattices. <i>Journal of Applied Physics</i> , 2011 , 110, 054506	2.5	61
84	COMPACT FORMULAE FOR NUMBER OF CONDUCTION CHANNELS IN VARIOUS TYPES OF GRAPHENE NANORIBBONS AT VARIOUS TEMPERATURES. <i>Modern Physics Letters B</i> , 2012 , 26, 1150004	1.6	28
83	Atomistic Study of the Lattice Thermal Conductivity of Rough Graphene Nanoribbons. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 2142-2147	2.9	25
82	A novel graphene nanoribbon field effect transistor with two different gate insulators. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2015 , 66, 133-139	3	24
81	Modeling comparison of graphene nanoribbon field effect transistors with single vacancy defect. <i>Superlattices and Microstructures</i> , 2016 , 97, 28-45	2.8	22
80	Stability analysis in multiwall carbon nanotube bundle interconnects. <i>Microelectronics Reliability</i> , 2012 , 52, 3026-3034	1.2	21
79	Improving ION/IOFF and sub-threshold swing in graphene nanoribbon field-effect transistors using single vacancy defects. <i>Superlattices and Microstructures</i> , 2015 , 86, 483-492	2.8	19
78	A 3D analytical modeling of tri-gate tunneling field-effect transistors. <i>Journal of Computational Electronics</i> , 2016 , 15, 820-830	1.8	11
77	Transient and steady state study of a rear-illuminated 6H-SiC Photoconductive Semiconductor Switch. <i>Optik</i> , 2016 , 127, 4615-4620	2.5	11
76	Calculation of Confined Phonon Spectrum in Narrow Silicon Nanowires Using the Valence Force Field Method. <i>Journal of Electronic Materials</i> , 2013 , 42, 2091-2097	1.9	11
75	Crosstalk Stability Analysis in Multilayer Graphene Nanoribbon Interconnects. <i>Circuits, Systems, and Signal Processing</i> , 2013 , 32, 2653-2666	2.2	11
74	Implementation of Open Boundary Problems in Photo-Conductive Antennas by Using Convolutional Perfectly Matched Layers. <i>IEEE Transactions on Antennas and Propagation</i> , 2016 , 64, 4919-4922	4.9	11
73	A comparative study of NEGF and DDMS models in the GAA silicon nanowire transistor. <i>International Journal of Electronics</i> , 2012 , 99, 1299-1307	1.2	10
72	A New SPICE Macro-Model for Simulation of Single Electron Circuits. <i>Journal of the Korean Physical Society</i> , 2010 , 56, 1202-1207	0.6	9
71	A computational study of vertical tunneling transistors based on graphene-WS2 heterostructure. <i>Journal of Applied Physics</i> , 2017 , 121, 214503	2.5	9

70	Modeling of a Vertical Tunneling Transistor Based on Graphene/MoS ₂ Heterostructure. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3459-3465	2.9	8
69	Design and simulation of a high power single mode 1550nm InGaAsP VCSELs. <i>IEICE Electronics Express</i> , 2011 , 8, 1096-1101	0.5	8
68	Effects of Stone-Wales defect on the electronic and transport properties of bilayer armchair graphene nanoribbons. <i>Superlattices and Microstructures</i> , 2016 , 100, 739-748	2.8	7
67	Investigation of quantum conductance in semiconductor single-wall carbon nanotubes: Effect of strain and impurity. <i>Journal of Applied Physics</i> , 2011 , 110, 064320	2.5	7
66	A silicon doped hafnium oxide ferroelectric p ⁺⁺ SOI tunneling field-effect transistor with steep subthreshold slope and high switching state current ratio. <i>AIP Advances</i> , 2016 , 6, 095010	1.5	7
65	Performance comparison of ideal and defected bilayer graphene nanoribbon FETs. <i>Superlattices and Microstructures</i> , 2017 , 111, 262-272	2.8	6
64	Electronic and transport properties of monolayer graphene defected by one and two carbon ad-dimers. <i>Applied Physics A: Materials Science and Processing</i> , 2014 , 116, 2057-2063	2.6	6
63	Role of 3D-paired pentagon/heptagon defects in electronic and transport properties of zigzag graphene nanoribbons. <i>Applied Physics A: Materials Science and Processing</i> , 2014 , 116, 295-301	2.6	6
62	Spin relaxation in graphene nanoribbons in the presence of substrate surface roughness. <i>Journal of Applied Physics</i> , 2016 , 120, 053904	2.5	6
61	Thermally induced spin-dependent current based on Zigzag Germanene Nanoribbons. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2017 , 86, 175-183	3	5
60	Graphene-Based Antidots for Thermoelectric Applications. <i>Journal of the Electrochemical Society</i> , 2011 , 158, K213	3.9	5
59	NUMERICAL INVESTIGATION ON THE TEMPERATURE DEPENDENCE OF THE CYLINDRICAL-GATE-ALL-AROUND Si-NW-FET. <i>Modern Physics Letters B</i> , 2011 , 25, 2269-2278	1.6	5
58	Engineered Nanopores-Based Armchair Graphene Nanoribbon FET With Resonant Tunneling Performance. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 5339-5346	2.9	5
57	Using Superlattice Structure in the Source of GNFET to Improve Its Switching Performance. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 1334-1339	2.9	4
56	Analytical Calculation of Energy levels of mono- and bilayer Graphene Quantum Dots Used as Light Absorber in Solar Cells. <i>Applied Physics A: Materials Science and Processing</i> , 2016 , 122, 1	2.6	4
55	Magnetization of bilayer graphene with interplay between monovacancy in each layer. <i>Journal of Applied Physics</i> , 2013 , 114, 084313	2.5	4
54	Small signal circuit modeling for semiconductor self-assembled quantum dot laser. <i>Optical Engineering</i> , 2011 , 50, 034202	1.1	4
53	PERFORMANCE EVALUATION OF SOURCE HETEROJUNCTION STRAINED CHANNEL GATE ALL AROUND NANOWIRE TRANSISTOR. <i>Modern Physics Letters B</i> , 2012 , 26, 1250076	1.6	4

52	An improved macro-model for simulation of single electron transistor (SET) using HSPICE 2009 ,		4
51	Novel Quantum Hydrodynamic Equations for Semiconductor Devices. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 1300-1304	1.4	4
50	Computational study of spin caloritronics in a pristine and defective antimonene nanoribbon. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2020 , 120, 114083	3	3
49	Performance improvement of junctionless field effect transistors using p-GaAs/AlGaAs heterostructure. <i>Superlattices and Microstructures</i> , 2017 , 110, 305-312	2.8	3
48	Analysis of Lattice Temperature Effects on a GaInP/6H-SiC Strained Quantum-Well Lasers. <i>Asian Journal of Chemistry</i> , 2013 , 25, 4715-4717	0.4	3
47	NOVEL STRUCTURES FOR CARBON NANOTUBE FIELD EFFECT TRANSISTORS. <i>International Journal of Modern Physics B</i> , 2009 , 23, 3871-3880	1.1	3
46	Tunable spherical graphene surface plasmon amplification by stimulated emission of radiation. <i>Journal of Nanophotonics</i> , 2019 , 13, 1	1.1	3
45	Full-Quantum Simulation of Graphene Self-Switching Diodes. <i>Chinese Physics Letters</i> , 2019 , 36, 067202	1.8	2
44	Effect of Stone-Wales defect on an armchair graphene nanoribbon-based photodetector. <i>Superlattices and Microstructures</i> , 2019 , 130, 127-138	2.8	2
43	Simulation and investigation of a back-triggered 6H-SiC high power photoconductive switch 2015 ,		2
42	A novel thermo-photovoltaic cell with quantum-well for high open circuit voltage. <i>Superlattices and Microstructures</i> , 2015 , 83, 61-70	2.8	2
41	Minimum length modulator design with a graphene-based plasmonic waveguide. <i>Applied Optics</i> , 2017 , 56, 4926-4933	0.2	2
40	Large signal analysis of double quantum well transistor laser. <i>Optical and Quantum Electronics</i> , 2013 , 45, 389-399	2.4	2
39	The noise equivalent circuit model of quantum-dot lasers. <i>Journal of Russian Laser Research</i> , 2012 , 33, 217-226	0.7	2
38	Analysis of carrier dynamic effects in transistor lasers. <i>Optical Engineering</i> , 2012 , 51, 024202	1.1	2
37	A new SPICE macro-model for simulation of single electron circuits 2009 ,		2
36	Quantum Corrections in the Drift-Diffusion Model. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 7247-7250		2
35	Normal-incidence near-1.55- μm Ge quantum dot photodetectors on Si substrate 2001 ,		2

34	Local impact of StoneWales defect on a single layer GNR/FET. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2020 , 384, 126170	2.3	2
33	A novel organicInorganic hybrid tandem solar cell with inverted structure. <i>Applied Physics A: Materials Science and Processing</i> , 2017 , 123, 1	2.6	1
32	Tight-binding model for the electronic properties of buckled triangular borophene. <i>Micro and Nano Letters</i> , 2019 , 14, 992-994	0.9	1
31	The effect of structural defects on the electron transport of MoS2 nanoribbons based on density functional theory. <i>Journal of Theoretical and Applied Physics</i> , 2019 , 13, 55-62	1.4	1
30	A seamless-pitched graphene nanoribbon field effect transistor. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2015 , 74, 414-420	3	1
29	Investigation of the electronic structure of tetragonal B3N3 under pressure. <i>Applied Physics A: Materials Science and Processing</i> , 2018 , 124, 1	2.6	1
28	Simulation analysis of inverted organic solar cells with grating structure: Undesirable effects of high absorption near grating anode. <i>Optik</i> , 2018 , 154, 453-458	2.5	1
27	Numerical simulation of vertical tunneling transistor with bilayer graphene as source and drain regions. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700155	1.6	1
26	Effect of Varying Aspect Ratio on Relative Stability for Graphene Nanoribbon Interconnects. <i>Applied Mechanics and Materials</i> , 2012 , 229-231, 205-209	0.3	1
25	A small signal circuit model of two mode InAs/GaAs quantum dot laser. <i>IEICE Electronics Express</i> , 2011 , 8, 245-251	0.5	1
24	TRIPLE-TUNNEL JUNCTION SINGLE ELECTRON TRANSISTOR (TTJ-SET). <i>Modern Physics Letters B</i> , 2011 , 25, 1487-1501	1.6	1
23	The non-equilibrium Green's function (NEGF) simulation of nanoscale lightly doped drain and source double gate MOSFETs 2012 ,		1
22	Investigation of breakdown voltage in InAlAs/InGaAs/InP HEMTs with different structures. <i>IEICE Electronics Express</i> , 2010 , 7, 1447-1452	0.5	1
21	Full quantum mechanical simulation of a novel nanoscale DG-MOSFET: 2D NEGF approach 2007 ,		1
20	Efficient implementation of the convective terms in the hydrodynamic equations. <i>Computer Methods in Applied Mechanics and Engineering</i> , 2005 , 194, 969-978	5.7	1
19	The most optimal barrier height of InGaN light-emitting diodes. <i>Applied Physics A: Materials Science and Processing</i> , 2021 , 127, 1	2.6	1
18	Doped silicon quantum dots as sources of coherent surface plasmons. <i>Journal of Optics (United Kingdom)</i> , 2018 , 20, 125001	1.7	1
17	GNR/FET with superlattice source, channel, and drain: SLSCD-GNR/FET. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2021 , 131, 114728	3	1

16	A Functional Study of a Bilayer Graphene Nanoribbon FET With Four Different Gate Insulators. <i>IEEE Nanotechnology Magazine</i> , 2019 , 18, 890-895	2.6	0
15	Large Signal Circuit Model of Two-Section Gain Lever Quantum Dot Laser. <i>Chinese Physics Letters</i> , 2012 , 29, 114207	1.8	0
14	Near-room-temperature spin caloritronics in a magnetized and defective zigzag MoS2 nanoribbon. <i>Journal of Computational Electronics</i> , 2020 , 19, 137-146	1.8	0
13	Spin FET Based on Graphene Nanoribbon in the Presence of Surface Roughness. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3437-3442	2.9	
12	Circuit Modeling of the Modulator Based on a Plasmonic Waveguide. <i>Journal of Nanoscience and Nanotechnology</i> , 2019 , 19, 5601-5607	1.3	
11	Pressure effect on the mechanical and electronic properties of B3N3: A first-principle study. <i>Physica C: Superconductivity and Its Applications</i> , 2018 , 548, 50-54	1.3	
10	Simulation of deep level traps effects in quantum well transistor laser. <i>Journal of Computational Electronics</i> , 2013 , 12, 812-815	1.8	
9	Effect of hotspot on THz radiation from Bi2Sr2CaCu2O8 intrinsic Josephson junctions. <i>Applied Physics A: Materials Science and Processing</i> , 2017 , 123, 1	2.6	
8	Effect of Varying Dielectric Constant on Relative Stability for Graphene Nanoribbon Interconnects. <i>Applied Mechanics and Materials</i> , 2012 , 229-231, 201-204	0.3	
7	Improving Elmore Model of RLC Networks for Applying to SWCNT Interconnects. <i>Applied Mechanics and Materials</i> , 2011 , 110-116, 5078-5084	0.3	
6	Reduced Master Equation for Modeling of Ferromagnetic Single-Electron Transistor. <i>Applied Mechanics and Materials</i> , 2011 , 110-116, 3103-3110	0.3	
5	An Investigation of the Geometrical Effects on the Thermal Conductivity of Graphene Antidot Lattices. <i>ECS Transactions</i> , 2011 , 35, 185-192	1	
4	Determining the Thickness of Barriers and Well of Resonance Tunneling Diodes by Specified I-V Characteristic. <i>Applied Mechanics and Materials</i> , 2011 , 110-116, 5464-5470	0.3	
3	Performance optimization of a plasmonic coupler based on a lossy transmission line. <i>Journal of Nanophotonics</i> , 2018 , 12, 1	1.1	
2	Influence of Physical Parameters on Microwave Noise Characteristics of Al0.3Ga0.7N/Al0.05Ga0.95N/GaN Composite-Channel HEMTs. <i>International Journal of Applied Physics and Mathematics</i> , 2013 , 442-445	0.4	
1	Analysis and simulation of asymmetrical nanoscale self-switching transistor. <i>International Journal of Modelling and Simulation</i> , 1-7	1.5	